

FQB34N20

N-Channel QFET® MOSFET

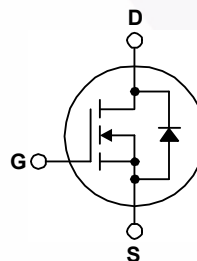
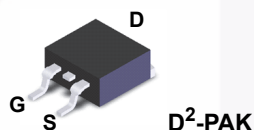
200 V, 31 A, 75 mΩ

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 31 A, 200 V, $R_{DS(on)} = 75 \text{ m}\Omega$ (Max.) @ $V_{GS} = 10 \text{ V}$, $I_D = 15.5 \text{ A}$
- Low Gate Charge (Typ. 60 nC)
- Low C_{rss} (Typ. 55 pF)
- 100% Avalanche Tested
- RoHS Compliant



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQB34N20TM_AM002	Unit
V_{DSS}	Drain-Source Voltage	200	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	31	A
	- Continuous ($T_C = 100^\circ\text{C}$)	20	A
I_{DM}	Drain Current - Pulsed (Note 1)	124	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	640	mJ
I_{AR}	Avalanche Current (Note 1)	31	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	18	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$) *	3.13	W
	Power Dissipation ($T_C = 25^\circ\text{C}$)	180	W
	- Derate above 25°C	1.43	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FQB34N20TM_AM002	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.7	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max.	62.5	
	Thermal Resistance, Junction to Ambient (* 1 in ² pad of 2 oz copper), Max.	40	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQB34N20	FQB34N20TM_AM002	D2-PAK	330mm	24mm	800

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	200	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	--	0.2	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 160\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 15.5\text{ A}$	--	0.06	0.075	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 15.5\text{ A}$	--	25	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	2400	3100	pF
C_{oss}	Output Capacitance		--	430	560	pF
C_{rss}	Reverse Transfer Capacitance		--	55	70	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 100\text{ V}, I_D = 34\text{ A},$ $R_G = 25\text{ }\Omega$	--	40	90	ns
t_r	Turn-On Rise Time		--	280	570	ns
$t_{d(off)}$	Turn-Off Delay Time		--	125	260	ns
t_f	Turn-Off Fall Time		--	115	240	ns
Q_g	Total Gate Charge	$V_{DS} = 160\text{ V}, I_D = 34\text{ A},$ $V_{GS} = 10\text{ V}$	--	60	78	nC
Q_{gs}	Gate-Source Charge		--	17	--	nC
Q_{gd}	Gate-Drain Charge		--	27	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	31	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	124	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 31 A	--	--	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 34 A, dI _F / dt = 100 A/μs	--	150	--	ns
Q _{rr}	Reverse Recovery Charge		--	0.95	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 1.0\text{ mH}$, $I_{AS} = 31\text{ A}$, $V_{DD} = 50\text{ V}$, $R_G = 25\text{ }\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 34\text{ A}$, $di/dt \leq 300\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Essentially independent of operating temperature

Typical Characteristics

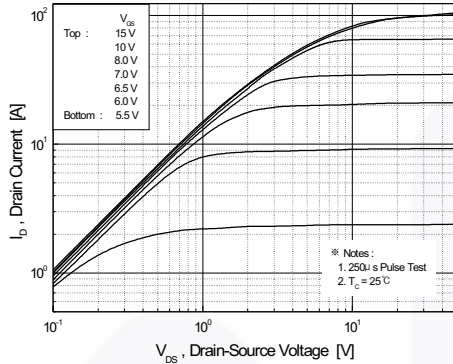


Figure 1. On-Region Characteristics

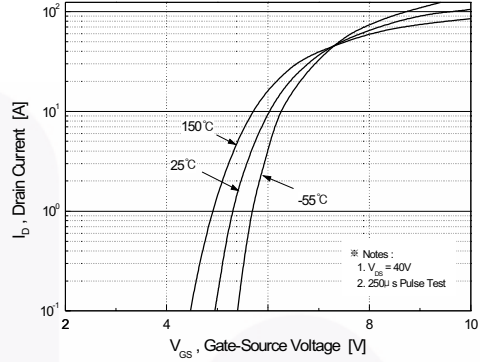


Figure 2. Transfer Characteristics

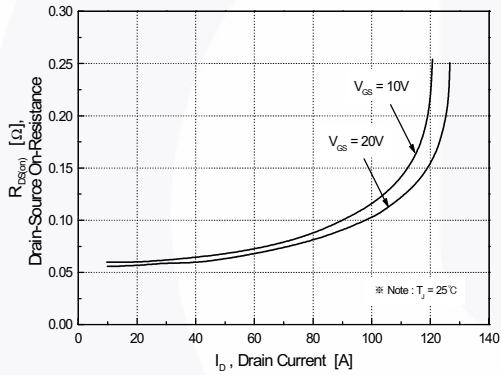


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

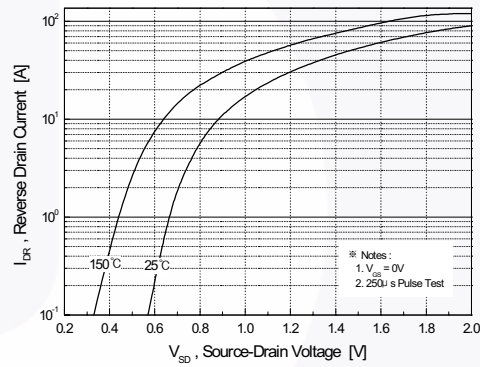


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

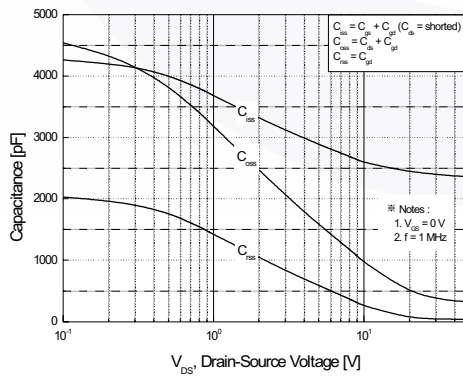


Figure 5. Capacitance Characteristics

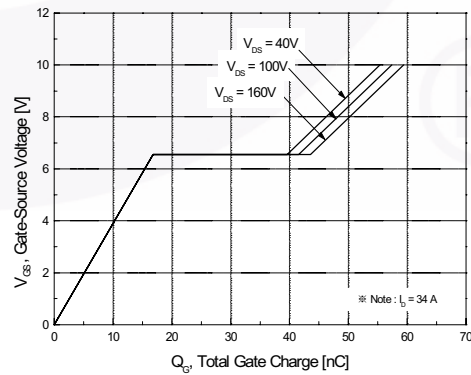


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

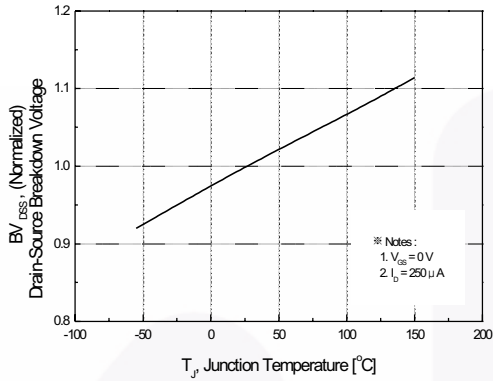


Figure 7. Breakdown Voltage Variation vs. Temperature

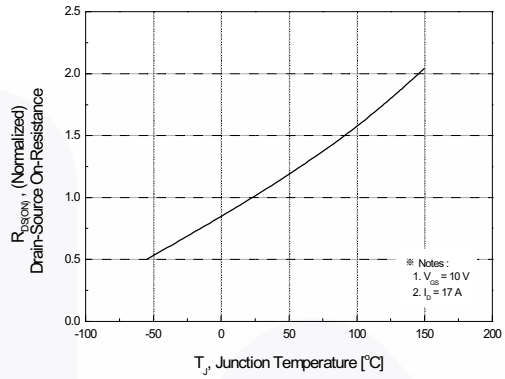


Figure 8. On-Resistance Variation vs. Temperature

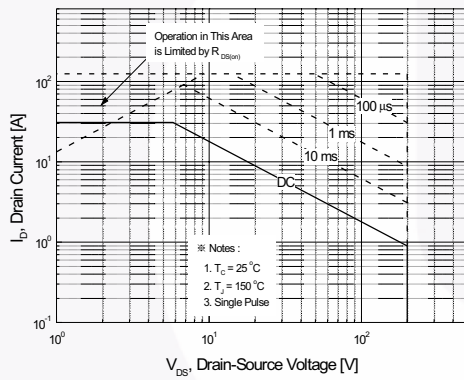


Figure 9. Maximum Safe Operating Area

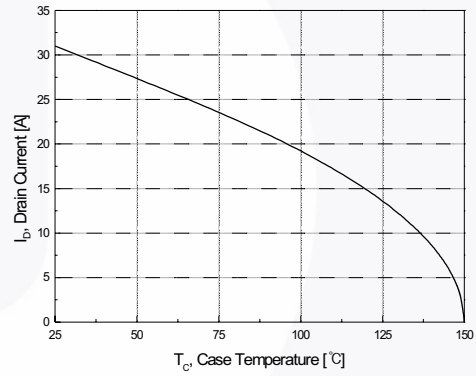


Figure 10. Maximum Drain Current vs. Case Temperature

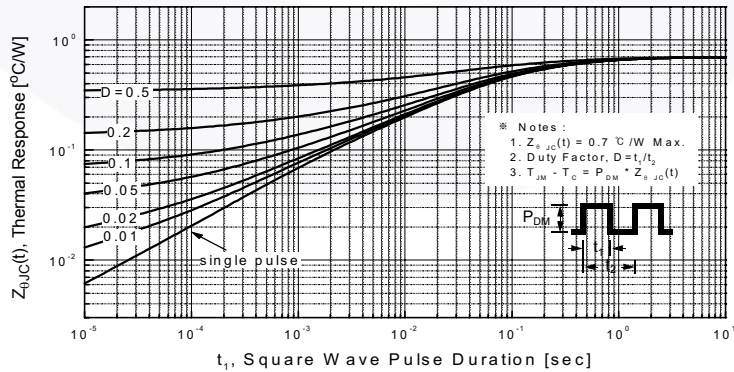


Figure 11. Transient Thermal Response Curve

Figure 12. Gate Charge Test Circuit & Waveform

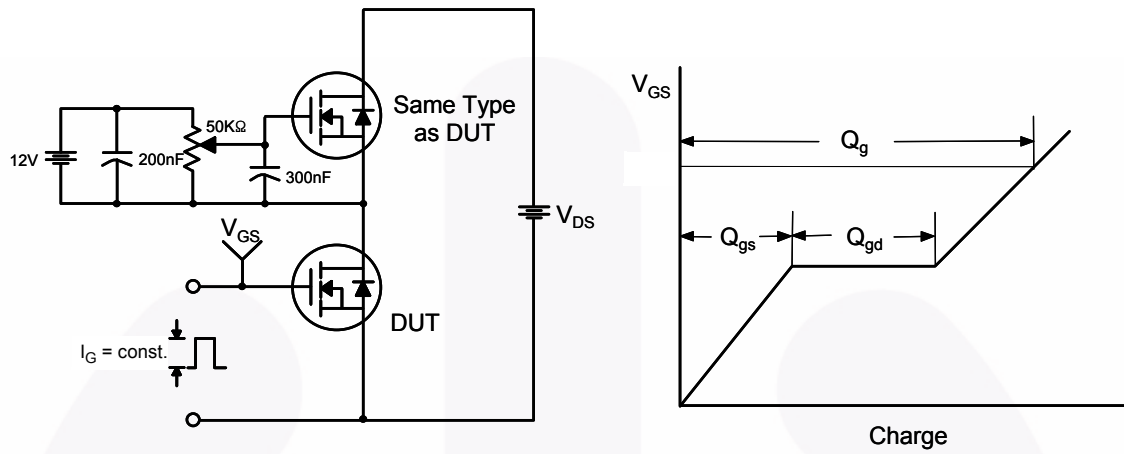


Figure 13. Resistive Switching Test Circuit & Waveforms

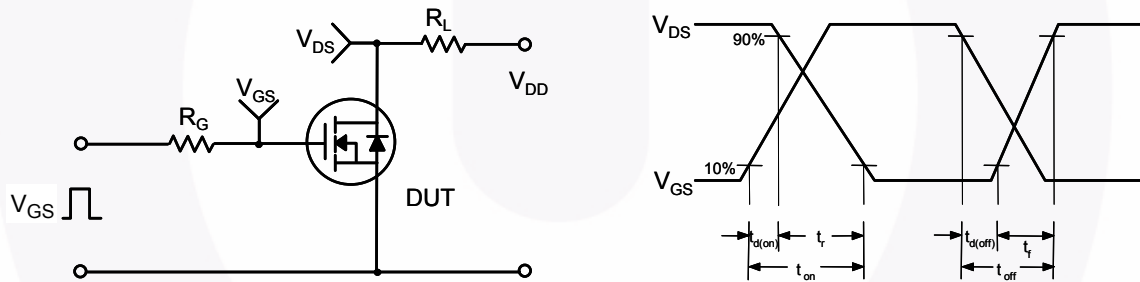


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

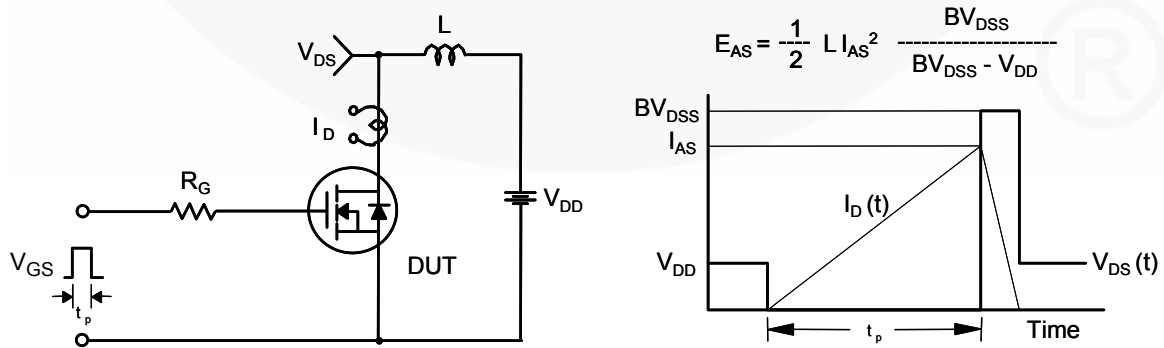
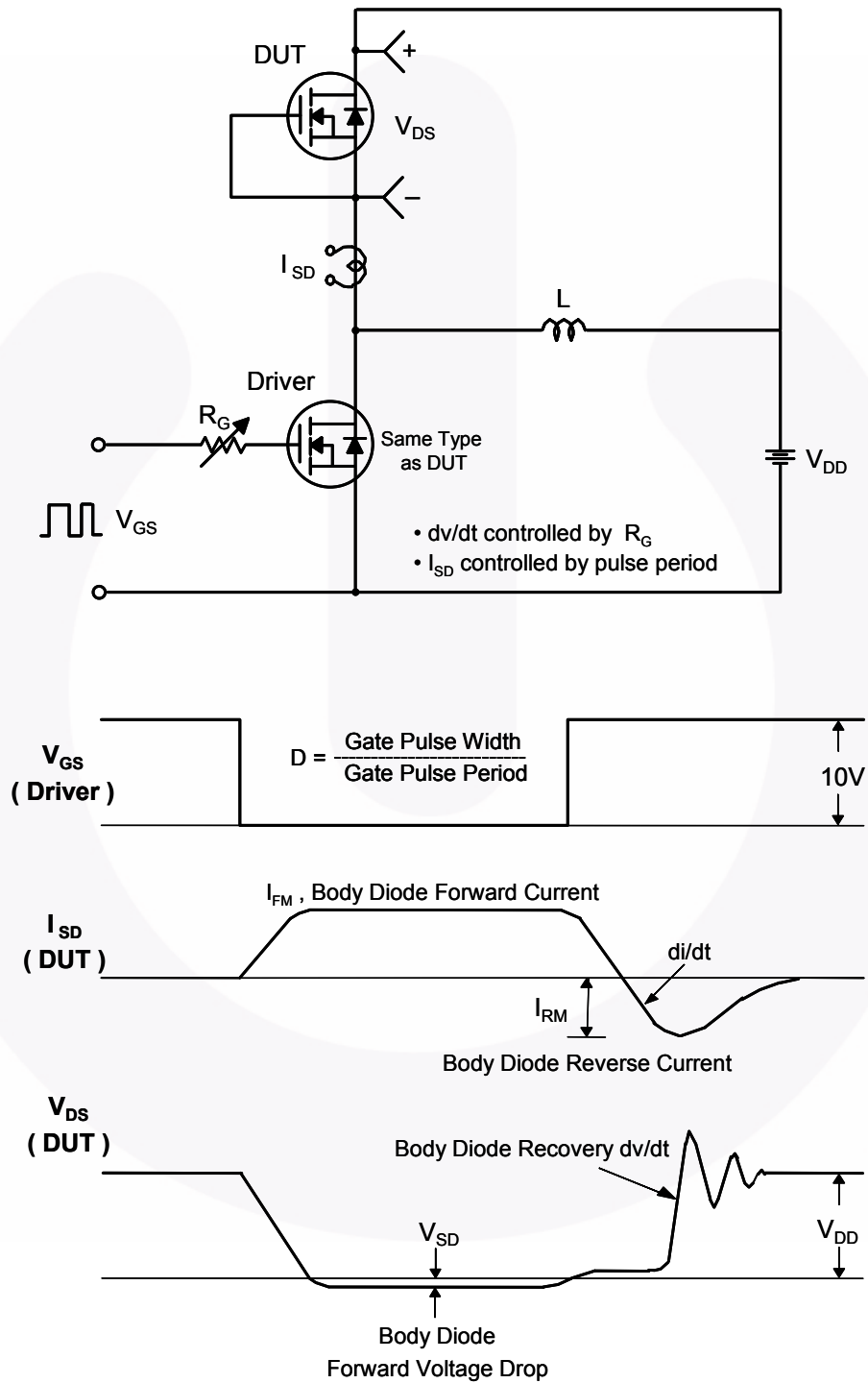


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

TO-263 2L (D²PAK)

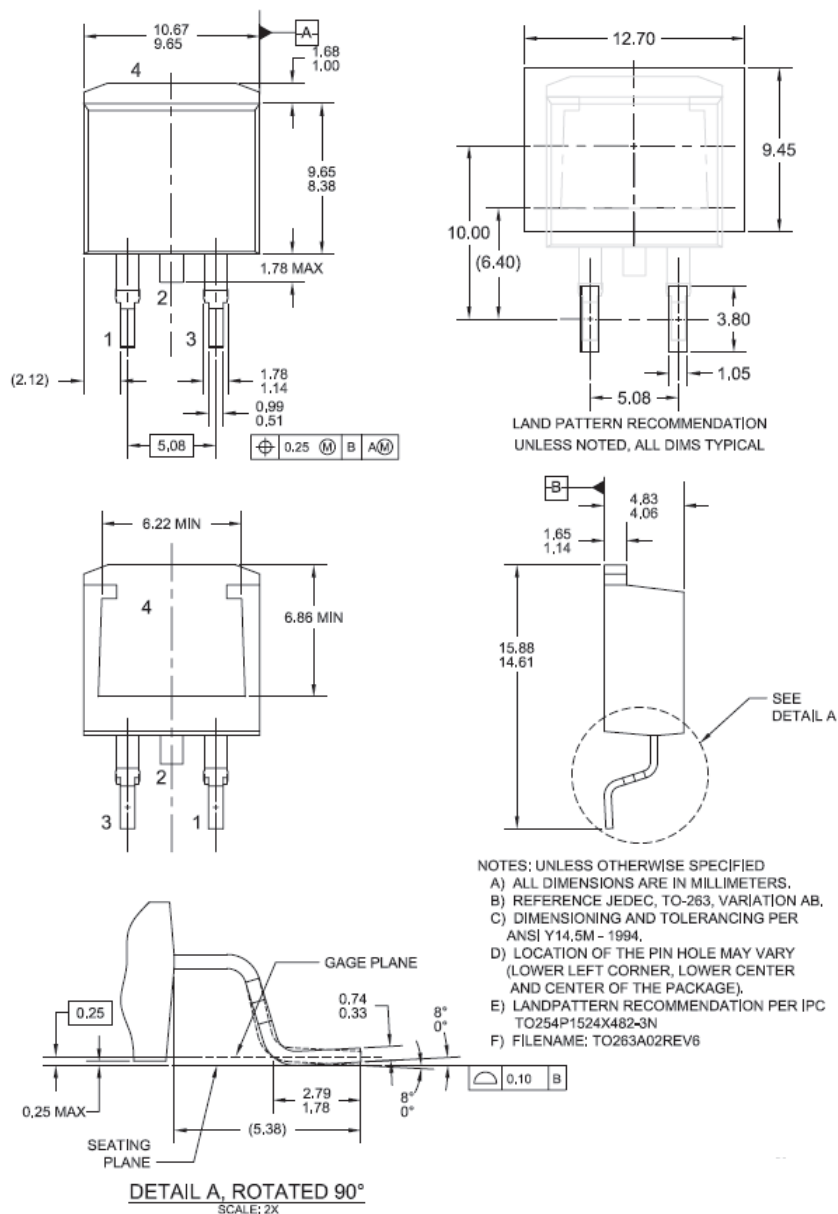


Figure 16. 2LD, TO263, Surface Mount

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

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http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT263-002

Dimension in Millimeters

